I have by certify that this correspondence is being deposited with the United States Postal Service as Frist Class Mail in an en el ope addressed to : Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on October 6, 2003. The cant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cinq-Mars mars 10/6/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

October 6, 2003 In re application of

Group Art Unit: John Bruley et al.

Examiner: Serial No. 10/605,258

International Business Machines Corporation 09/18/2003 Filed:

2070 Route 52

Hopewell Junction, NY 12533

TITLE: Site-Specific Methodology for Localization and Analyzing Junction Defects in MOSFET Devices

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

John Bruley et al.

Tiffany Townsend, Attorney Registration No. 43,199

Telephone No. 845-894-3668

FIS920030145US1 10/605,258

SERIAL NO.: ATTY. DOCKET NO.: U.S. DEPARTMENT OF COMMERCE FIS920030145US1 PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE APPLICANT: John Bruley et al. STATEMENT BY APPLICANT (Use several sheets if necessary) **GROUP:** FILING DATE: (37 CFR 1.98(b))

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